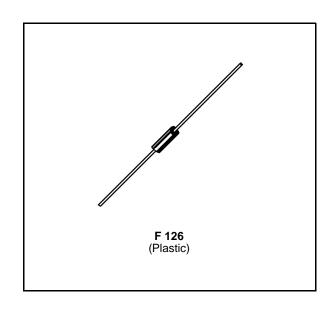


# FAST RECOVERY RECTIFIER DIODES

#### **FAST RECOVERY RECTIFIER**

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING



### **SUITABLE APPLICATION**

- FREE WHEELING DIODE IN CONVERTERS AND MOTORS CIRCUITS
- RECTIFIER IN S.M.P.S.

# **ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Value	Unit	
I <sub>FRM</sub>	Repetive Peak Forward Current	t <sub>p</sub> ≤ 10μs	30	Α
I <sub>F (AV)</sub>	Average Forward Current*	$T_a = 70^{\circ}C$ $\delta = 0.5$	1	А
I <sub>FSM</sub>	Surge non Repetitive Forward Current	t <sub>p</sub> = 10ms Sinusoidal	30	А
Р	Power Dissipation*	Ta = 70°C	1.33	W
T <sub>stg</sub> T <sub>j</sub>	Storage and Junction Temperature Range		- 40 to +150 - 40 to + 150	°C

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	400	٧
V <sub>RSM</sub>	Non Repetitive Peak Reverse Voltage	440	V

# THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R <sub>th (j - a)</sub>	Junction-ambient*	60	°C/W

<sup>\*</sup> On infinite heatsink with 10mm lead length.

August 1998 Ed : 1A 1/5

# **ELECTRICAL CHARACTERISTICS**

# STATIC CHARACTERISTICS

Symbol	Test Conditions			Тур.	Max.	Unit
I <sub>R</sub>	T <sub>j</sub> = 25°C	$V_R = V_{RRM}$			20	μΑ
	T <sub>j</sub> = 100°C				0.5	mA
$V_{F}$	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A			1.5	V
	T <sub>j</sub> = 100°C				1.4	

#### RECOVERY CHARACTERISTICS

Symbol	Test Conditions					Тур.	Max.	Unit
t <sub>rr</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A	$di_F/dt = -15A/\mu s$	$V_R = 30V$			55	ns
	T <sub>j</sub> = 25°C	I <sub>F</sub> = 0.5A	I <sub>R</sub> = 1A	$I_{rr} = 0.25A$			25	

# TURN-OFF SWITCHING CHARACTERISTICS (Without Series inductance)

Symbol	Test Conditions					Тур.	Max.	Unit
t <sub>IRM</sub>	$di_F/dt = -50A/\mu s$	T <sub>j</sub> = 100°C	V <sub>CC</sub> = 200 V	$I_F = 1A$		35	50	ns
I <sub>RM</sub>	$di_F/dt = -50A/\mu s$	$L_p \le 0.05 \; \mu A$	See figure 12			1.5	2	Α

To evaluate the conduction losses use the following equations:

$$V_F = 1.05 + 0.145 I_F$$
  $P = 1.05 \times I_{F(AV)} + 0.145 I_{F^2(RMS)}$ 

Figure 1. Maximum average power dissipation versus average forward current.

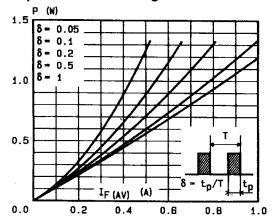


Figure 2. Average forward current versus ambient temperature.

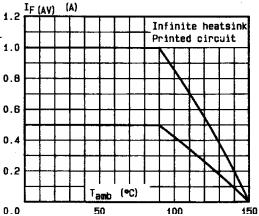
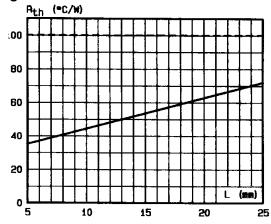


Figure 3. Thermal resistance versus lead length.



Mounting n°1
INFINITE HEATSINK

Mounting n°2 PRINTED CIRCUIT

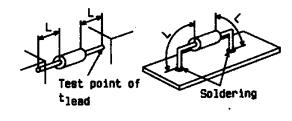


Figure 4. Transient thermal impedance junction-ambient for mounting  $n^2$  versus pulse duration (L = 10 mm).

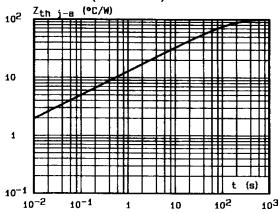


Figure 5. Peak forward current versus peak forward voltage drop (maximum values).

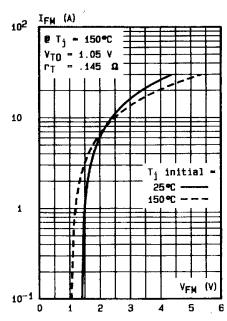


Figure 7. Recovery time versus dif/dt.

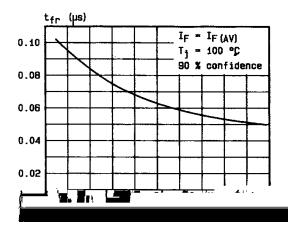


Figure 8. Peak forward voltage versus dif/dt.

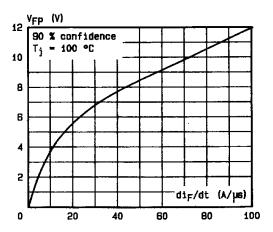


Figure 9. Peak reverse current versus di<sub>F</sub>/dt.

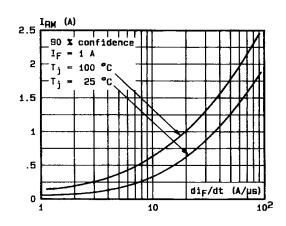


Figure 10. Recovered charge versus di<sub>F</sub>/dt (typical values).

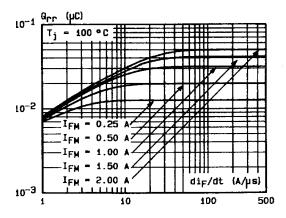


Figure 11. Dynamic parameters versus junction temperature.

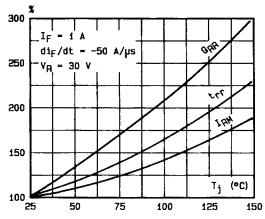
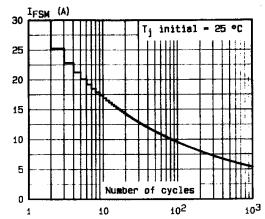


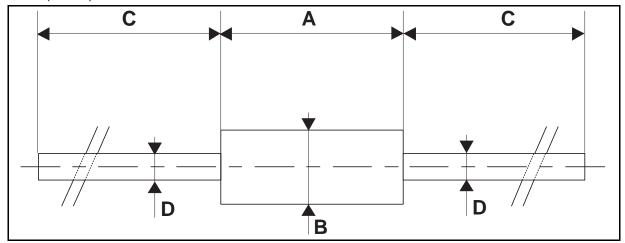
Figure 12. Non repetitive surge peak current versus number of cycles.



5/

#### **PACKAGE MECHANICAL DATA**

#### F 126 (Plastic)



REF.	DIMENSIONS							
	Mi	illimete	ers		Inches	i		
	Min.	Тур.	Max.	Min.	Max.			
Α	6.05	6.20	6.35	0.238	0.244	0.250		
В	2.95	3.00	3.05	0.116	0.118	0.120		
С	26		31	1.024		1.220		
D	0.76	0.81	0.86	0.030	0.032	0.034		

■ Marking: type number

■ Cooling method: by convection (method A)

■ Weight: 0.393g

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied.

STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval

of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 1998 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - France - Germany - Italy - Japan - Korea - Malaysia - Malta - Mexico - Morocco - The Netherlands Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.

